

Silicon Switching Diode

1N4607

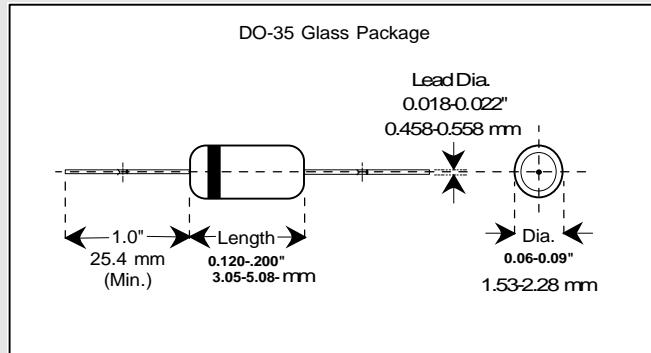
DO-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	85 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	200	mAmps	
Peak Surge Current ($t_{peak} = 1$ sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation $T_L = 50$ °C, L = 3/8" from body	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +200	° C	
Storage Temperature Range	T _{St}	-65 to +200	° C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 µA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	µA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED



6 Lake Street - Lawrence, MA 01841

Tel: 978-681-0392 - Fax: 978-681-9135